NLAS4053

Analog Multiplexer/ Demultiplexer

Triple 2:1 Analog Switch−Multiplexer Improved Process, Sub−Micron Silicon Gate CMOS

ON Semiconductor®

http://onsemi.com

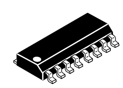
The NLAS4053 is an improved version of the MC14053 and MC74HC4053 fabricated in sub−micron Silicon Gate CMOS technology for lower $R_{DS(on)}$ resistance and improved linearity with low current. This device may be operated either with a single supply or dual supply up to ±3.0 V to pass a 6 V_{PP} signal without coupling capacitors.

When operating in single supply mode, it is only necessary to tie V_{EE}, pin 7 to ground. For dual supply operation, V_{EE} is tied to a negative voltage, not to exceed maximum ratings. Pin for pin compatible with all industry standard versions of '4053.'

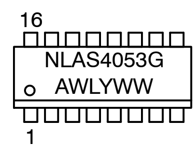
Features

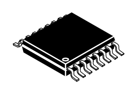
- Improved $R_{DS(on)}$ Specifications
- Pin for Pin Replacement for MAX4053 and MAX4053A
  - One Half the Resistance Operating at 5.0 Volts
- Single or Dual Supply Operation
  - Single 3−5 Volt Operation, or Dual ±3.0 Volt Operation
  - With V_{CC} of 3.0 to 3.3 V, Device Can Interface with 1.8 V Logic, No Translators Needed
  - Address and Inhibit Pins are Over−Voltage Tolerant and May Be Driven Up +6.0 V Regardless of V_{CC}
  - Greatly Improved Noise Margin Over MAX4053 and MAX4053A
- Improved Linearity Over Standard HC4053 Devices
- Popular SOIC and the Space Saving TSSOP Packages
- Pb−Free Packages are Available*

MARKING DIAGRAMS

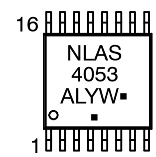


SOIC−16
D SUFFIX
CASE 751B





TSSOP−16
DT SUFFIX
CASE 948F



A	=	Assembly Location
L, WL	=	Wafer Lot
Y	=	Year
W, WW	=	Work Week
G	=	Pb−Free Package
▪	=	Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

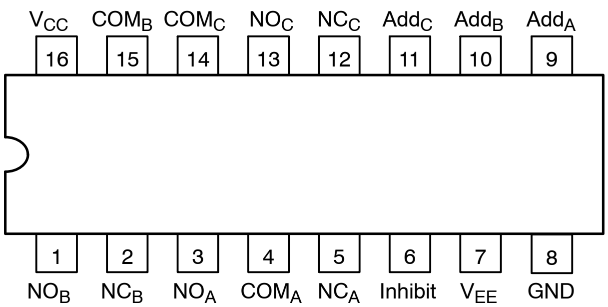


Figure 1. Pin Connection
(Top View)

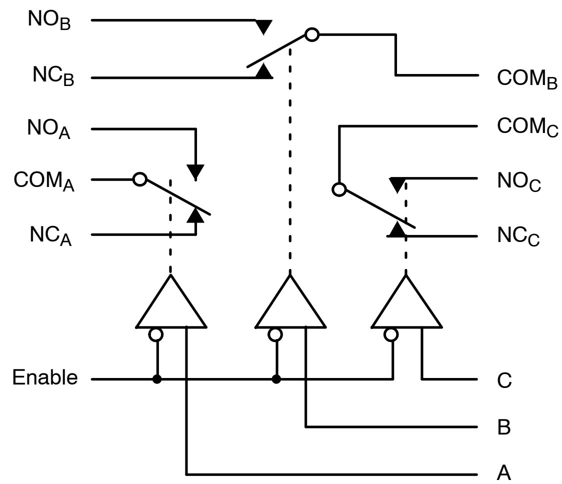


Figure 2. Logic Diagram

TRUTH TABLE

Inhibit	Address			ON SWITCHES*
	C	**B**	**A**	
1	X don't care	X don't care	X don't care	All switches open
0	0	0	0	COM_A–NC_A, COM_B–NC_B, COM_C–NC_C
0	0	0	1	COM_A–NO_A, COM_B–NC_B, COM_C–NC_C
0	0	1	0	COM_A–NC_A, COM_B–NO_B, COM_C–NC_C
0	0	1	1	COM_A–NO_A, COM_B–NO_B, COM_C–NC_C
0	1	0	0	COM_A–NC_A, COM_B–NC_B, COM_C–NO_C
0	1	0	1	COM_A–NO_A, COM_B–NC_B, COM_C–NO_C
0	1	1	0	COM_A–NC_A, COM_B–NO_B, COM_C–NO_C
0	1	1	1	COM_A–NO_A, COM_B–NO_B, COM_C–NO_C

*NO, NC, and COM pins are identical and interchangeable. Either may be considered an input or output; signals pass equally well in either direction.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{EE}	Negative DC Supply Voltage	(Referenced to GND)	−7.0 to +0.5	V
V_{CC}	Positive DC Supply Voltage (Note 1)	(Referenced to GND) (Referenced to V_{EE})	−0.5 to +7.0 −0.5 to +7.0	V
V_{IS}	Analog Input Voltage		V_{EE} −0.5 to V_{CC} +0.5	V
V_{IN}	Digital Input Voltage	(Referenced to GND)	−0.5 to 7.0	V
I	DC Current, Into or Out of Any Pin		±50	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	143 164	°C/W
P_D	Power Dissipation in Still Air,	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% − 35%	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 >1000	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The absolute value of V_{CC} ± $|V_{EE}| \leq 7.0$.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{EE}	Negative DC Supply Voltage	(Referenced to GND)	−5.5	GND	V
V_{CC}	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V_{EE})	2.5 2.5	5.5 6.6	V
V_{IS}	Analog Input Voltage		V_{EE}	V_{CC}	V
V_{IN}	Digital Input Voltage	(Note 6) (Referenced to GND)	0	5.5	V
T_A	Operating Temperature Range, All Package Types		−55	125	°C
t_r, t_f	Input Rise/Fall Time (Channel Select or Enable Inputs)	V_{CC} = 3.0 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

6. Unused digital inputs may not be left open. All digital inputs must be tied to a high−logic voltage level or a low−logic input voltage level.

ORDERING INFORMATION

Device	Package	Shipping†
NLAS4053DG	SOIC−16 (Pb−Free)	48 Units / Rail
NLAS4053DR2	SOIC−16	2500 Tape & Reel
NLAS4053DR2G	SOIC−16 (Pb−Free)	2500 Tape & Reel
NLAS4053DT	TSSOP−16*	96 Units / Rail
NLAS4053DTG	TSSOP−16*	96 Units / Rail
NLAS4053DTR2	TSSOP−16*	2500 Tape & Reel
NLAS4053DTR2G	TSSOP−16*	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

DC CHARACTERISTICS − Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} V	Guaranteed Limit			Unit
				−55 to 25°C	≤85°C	≤125°C	
V_{IH}	Minimum High−Level Input Voltage, Address and Inhibit Inputs		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	V
V_{IL}	Maximum Low−Level Input Voltage, Address and Inhibit Inputs		2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V
I_{IN}	Maximum Input Leakage Current, Address or Inhibit Inputs	V_{IN} = 6.0 or GND	0 V to 6.0 V	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and $V_{IS} = V_{CC}$ or GND	6.0	4.0	40	80	μA

DC ELECTRICAL CHARACTERISTICS − Analog Section

Symbol	Parameter	Test Conditions	V_{CC} V	V_{EE} V	Guaranteed Limit			Unit
					−55 to 25°C	≤85°C	≤125°C	
R_{ON}	Maximum "ON" Resistance	$V_{IN} = V_{IL}$ or V_{IH} $V_{IS} = V_{EE}$ to V_{CC} $\|I_S\|$ = 10 mA (Figures 4 thru 9)	3.0 4.5 3.0	0 0 −3.0	86 37 26	108 46 33	120 55 37	Ω
ΔR_{ON}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{IN} = V_{IL}$ or V_{IH}, V_{IS} = 2.0 V V_{IS} = 3.5 V $\|I_S\|$ = 10 mA, V_{IS} = 2.0 V	3.0 4.5 3.0	0 0 −3.0	15 13 10	20 18 15	20 18 15	Ω
$R_{flat(ON)}$	COM−NO On−Resistance Flatness	V_{com} 1, 2, 3.5 V V_{com} −2, 0, 2 V $\|I_S\|$ = 10 mA	4.5 3.0	0 −3.0	4 2	4 2	5 3	Ω
$I_{NC(OFF)}$ $I_{NO(OFF)}$	Maximum Off−Channel Leakage Current	Switch Off $V_{IN} = V_{IL}$ or V_{IH} $V_{IO} = V_{CC}$ −1.0 V or V_{EE} +1.0 V (Figure 17)	6.0 3.0	0 −3.0	0.1 0.1	5.0 5.0	100 100	nA
$I_{COM(ON)}$	Maximum On−Channel Leakage Current, Channel− to−Channel	Switch On $V_{IO} = V_{CC}$ −1.0 V or V_{EE} +1.0 V (Figure 17)	6.0 3.0	0 −3.0	0.1 0.1	5.0 5.0	100 100	nA

AC CHARACTERISTICS (Input $t_r = t_f = 3$ ns)

Symbol	Parameter	Test Conditions	V_{CC} V	V_{EE} V	Guaranteed Limit –55 to 25°C Min	Typ*	≤85°C	≤125°C	Unit
t_{BBM}	Minimum Break–Before–Make Time	$V_{IN} = V_{IL}$ or V_{IH} $V_{IS} = V_{CC}$ R_L = 300 Ω, C_L = 35 pF (Figure 19)	3.0 4.5 3.0	0.0 0.0 –3.0	1.0 1.0 1.0	6.5 5.0 3.5	– – –	– – –	ns

*Typical Characteristics are at 25°C.

AC CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f = 3$ ns)

Symbol	Parameter	V_{CC} V	V_{EE} V	Guaranteed Limit –55 to 25°C Min	Typ	Max	≤85°C Min	Max	≤125°C Min	Max	Unit
t_{TRANS}	Transition Time (Address Selection Time) (Figure 18)	2.5 3.0 4.5 3.0	0 0 0 –3.0			40 28 23 23		45 30 25 25		50 35 30 28	ns
t_{ON}	Turn–on Time (Figures 14, 15, 20, and 21) Enable to N_O or N_C	2.5 3.0 4.5 3.0	0 0 0 –3.0			40 28 23 23		45 30 25 25		50 35 30 28	ns
t_{OFF}	Turn–off Time (Figures 14, 15, 20, and 21) Enable to N_O or N_C	2.5 3.0 4.5 3.0	0 0 0 –3.0			40 28 23 23		45 30 25 25		50 35 30 28	ns

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{IN}	Maximum Input Capacitance,Select Inputs	8	pF
C_{NO} or C_{NC}	Analog I/O	10	
C_{COM}	Common I/O	10	
$C_{(ON)}$	Feedthrough	1.0	

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

Symbol	Parameter	Condition	V_{CC} V	V_{EE} V	Typ 25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response	V_{IS} = ½ ($V_{CC} - V_{EE}$) Source Amplitude = 0 dBm (Figures 10 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 –3.0	145 165 180 180	MHz
V_{ISO}	Off–Channel Feedthrough Isolation	f = 100 kHz; V_{IS} = ½ ($V_{CC} - V_{EE}$) Source = 0 dBm (Figures 12 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 –3.0	–93 –93 –93 –93	dB
V_{ONL}	Maximum Feedthrough On Loss	V_{IS} = ½ ($V_{CC} - V_{EE}$) Source = 0 dBm (Figures 10 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 –3.0	–2 –2 –2 –2	dB
Q	Charge Injection	$V_{IN} = V_{CC}$ to V_{EE}, f_{IS} = 1 kHz, $t_r = t_f$ = 3 ns R_{IS} = 0 Ω, C_L= 1000 pF, Q = $C_L * \Delta V_{OUT}$ (Figures 16 and 23)	5.0 3.0	0.0 –3.0	9.0 12	pC
THD	Total Harmonic Distortion THD + Noise	f_{IS} = 1 MHz, R_L = 10 KΩ, C_L = 50 pF, V_{IS} = 5.0 V_{PP} sine wave V_{IS} = 6.0 V_{PP} sine wave (Figure 13)	 6.0 3.0	 0.0 –3.0	 0.10 0.05	%

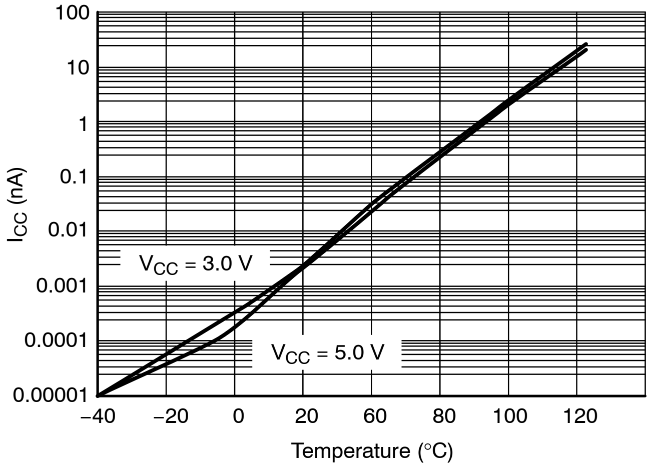


Figure 3. I_{CC} versus Temp, V_{CC} = 3 V and 5 V

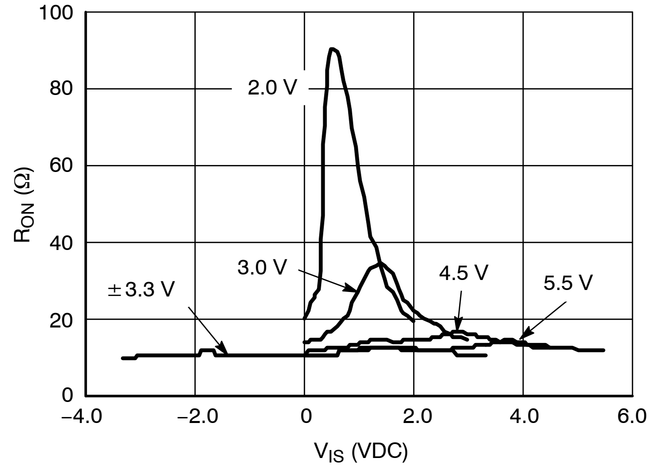


Figure 4. R_{ON} versus V_{CC}, Temp = 25°C

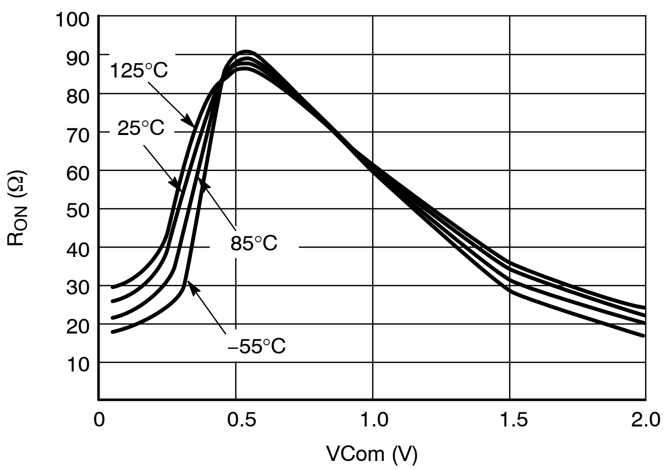


Figure 5. Typical On Resistance
V_{CC} = 2.0 V, V_{EE} = 0 V

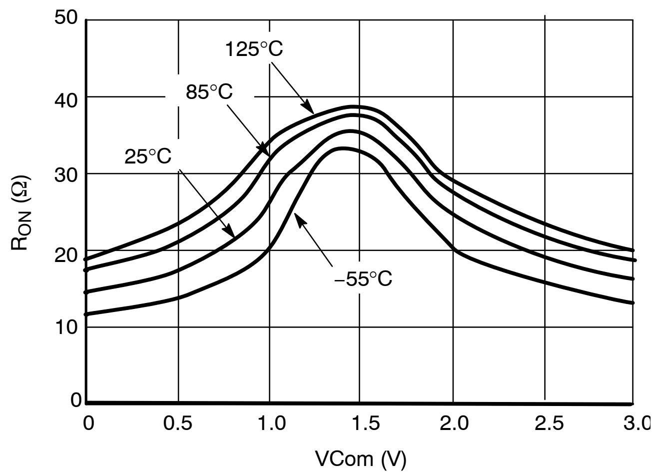


Figure 6. Typical On Resistance
V_{CC} = 3.0 V, V_{EE} = 0 V

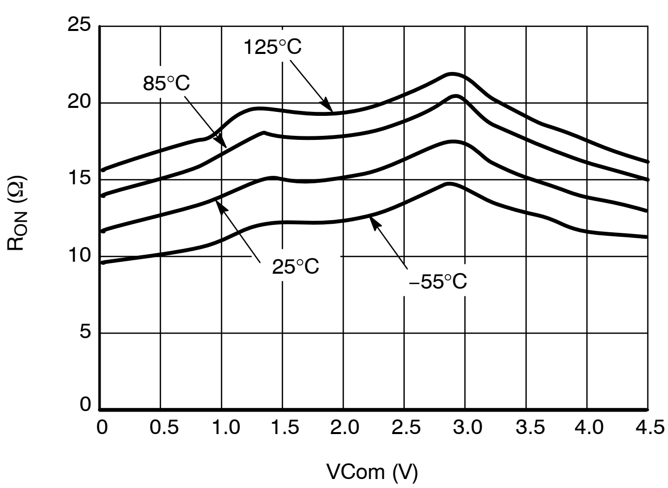


Figure 7. Typical On Resistance
V_{CC} = 4.5 V, V_{EE} = 0 V

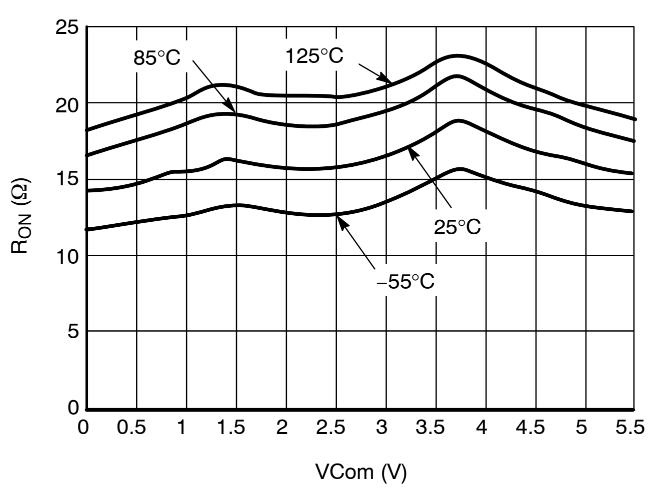


Figure 8. Typical On Resistance
V_{CC} = 5.5 V, V_{EE} = 0 V

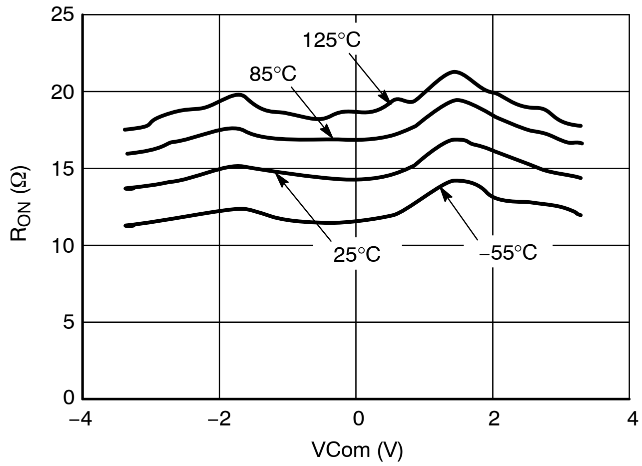


Figure 9. Typical On Resistance
V_{CC} = 3.3 V, V_{EE} = −3.3 V

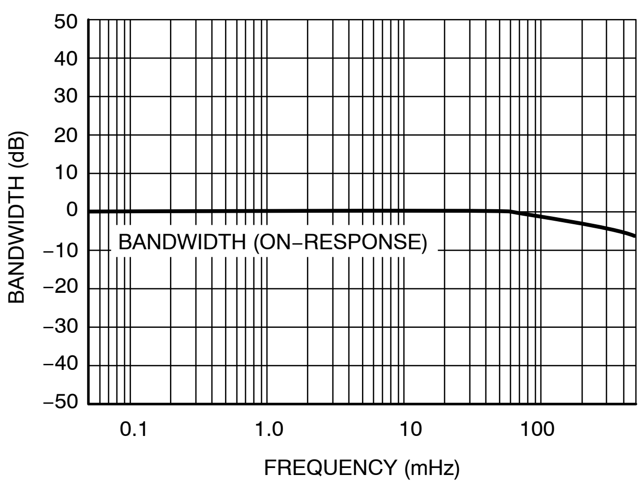


Figure 10. Bandwidth

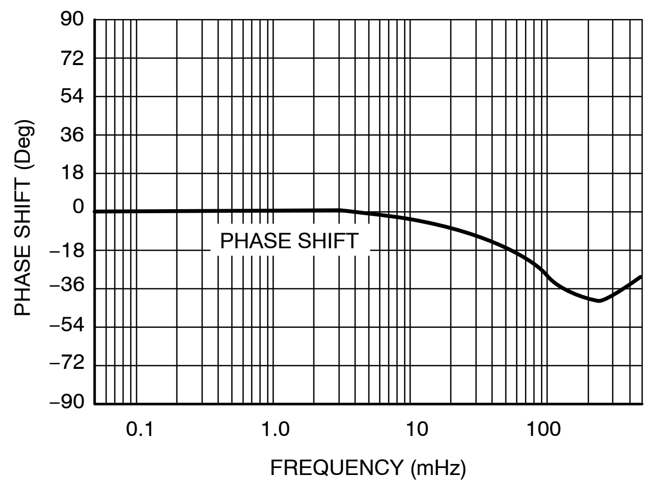


Figure 11. Phase Shift

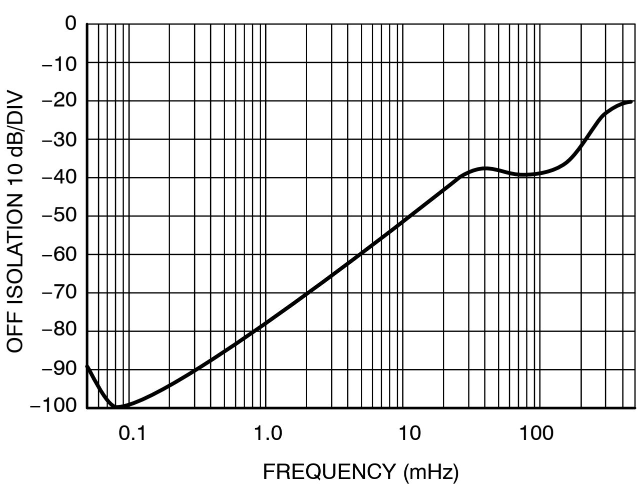


Figure 12. Off Isolation

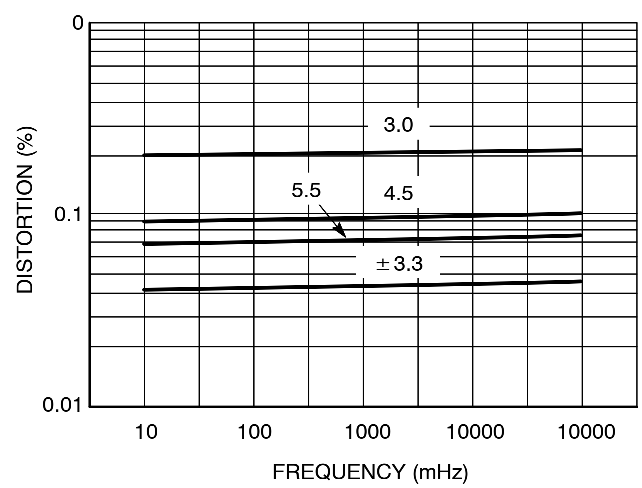


Figure 13. Total Harmonic Distortion

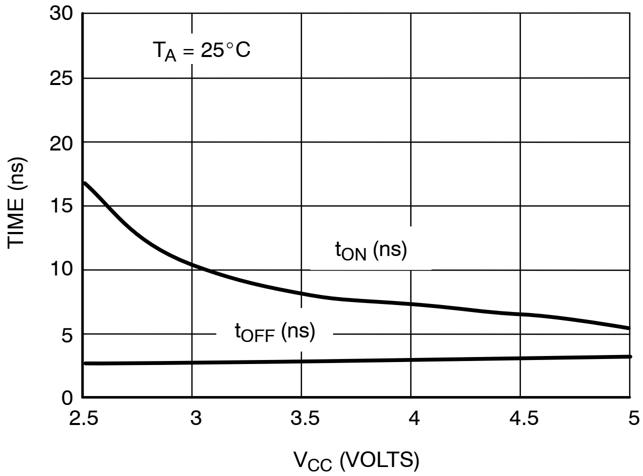


Figure 14. t_{ON} and t_{OFF} versus V_{CC}

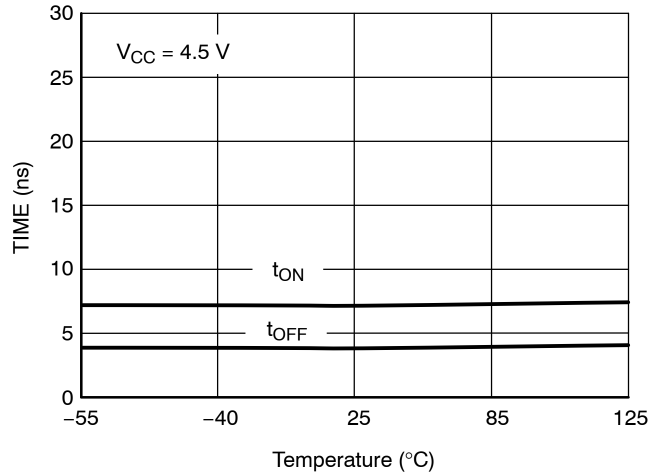


Figure 15. t_{ON} and t_{OFF} versus Temp

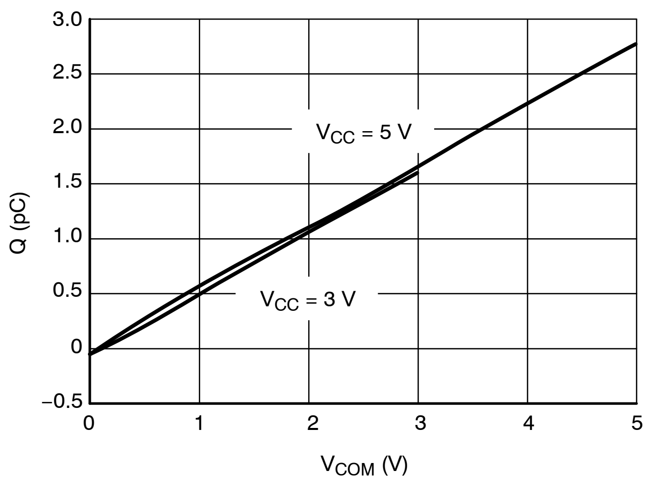


Figure 16. Charge Injection versus COM Voltage

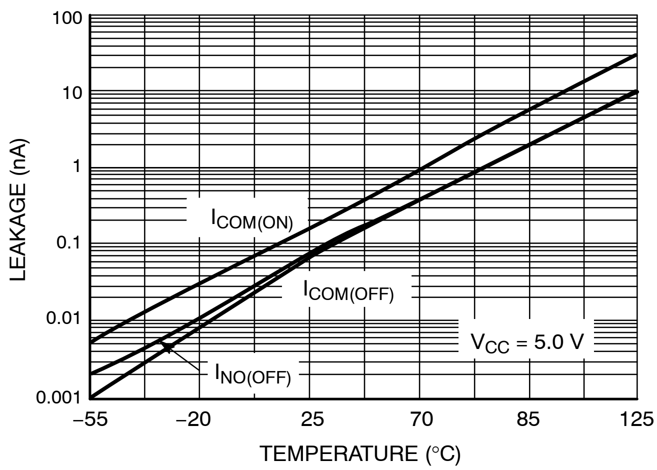


Figure 17. Switch Leakage versus Temperature

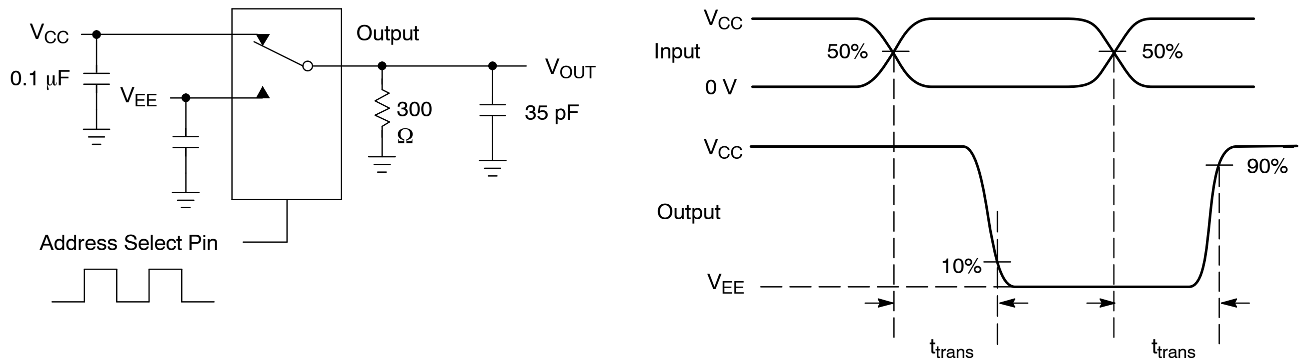


Figure 18. Channel Selection Propagation Delay

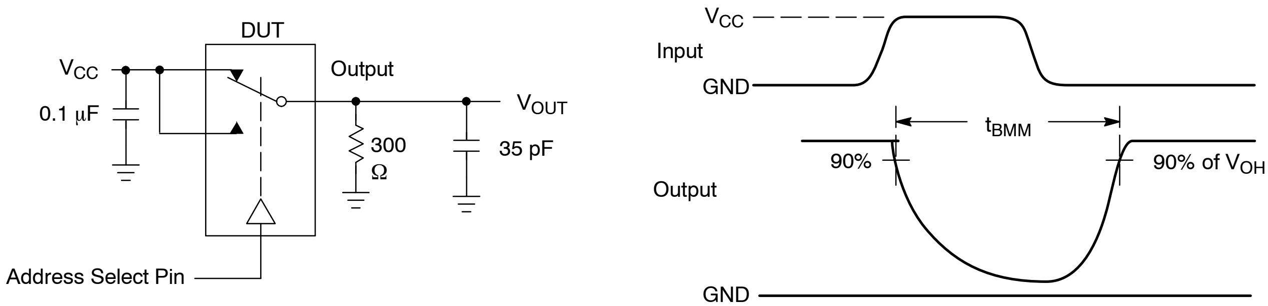


Figure 19. t_{BBM} (Time Break−Before−Make)

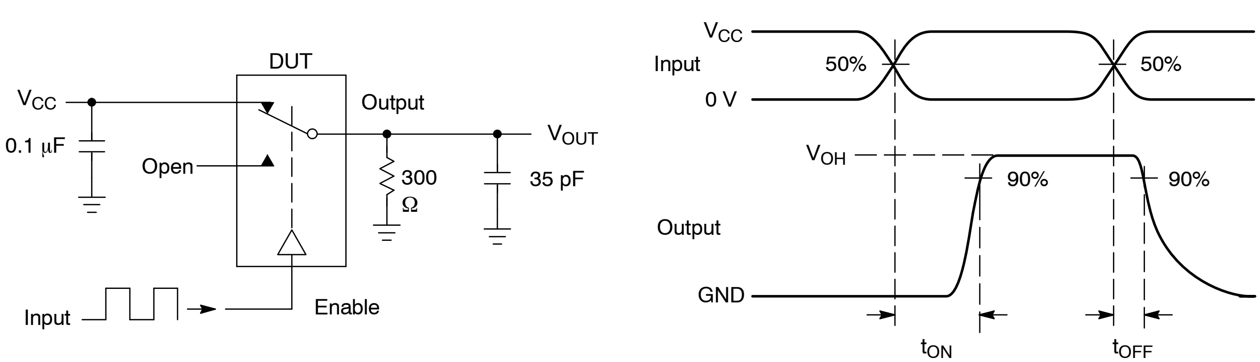


Figure 20. t_{ON}/t_{OFF}

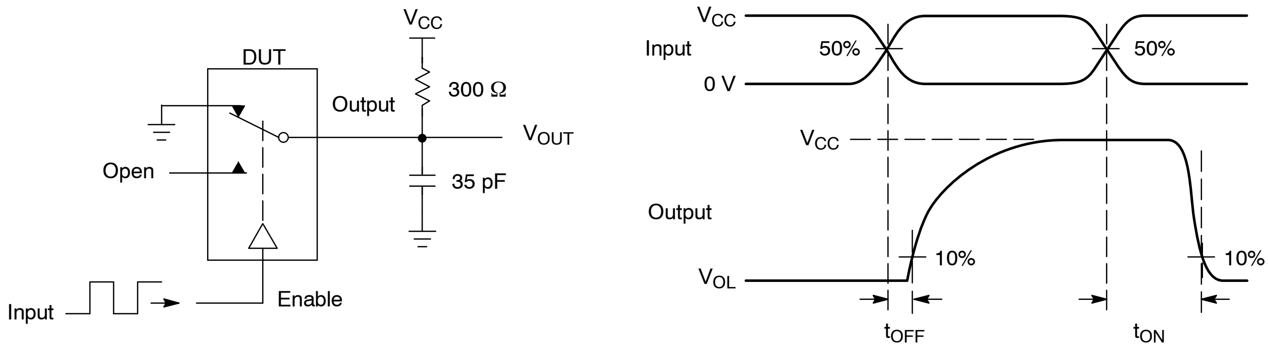
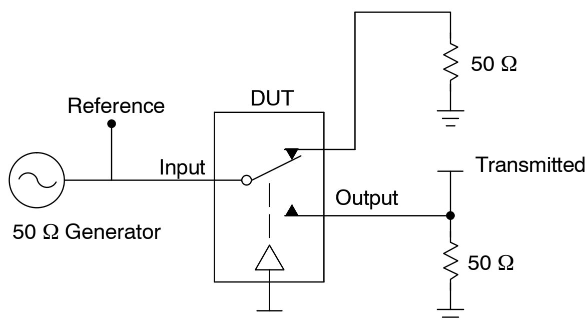


Figure 21. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO}, Bandwidth and V_{ONL} are independent of the input signal direction.

V_{ISO} = Off Channel Isolation = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz

V_{ONL} = On Channel Loss = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 22. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

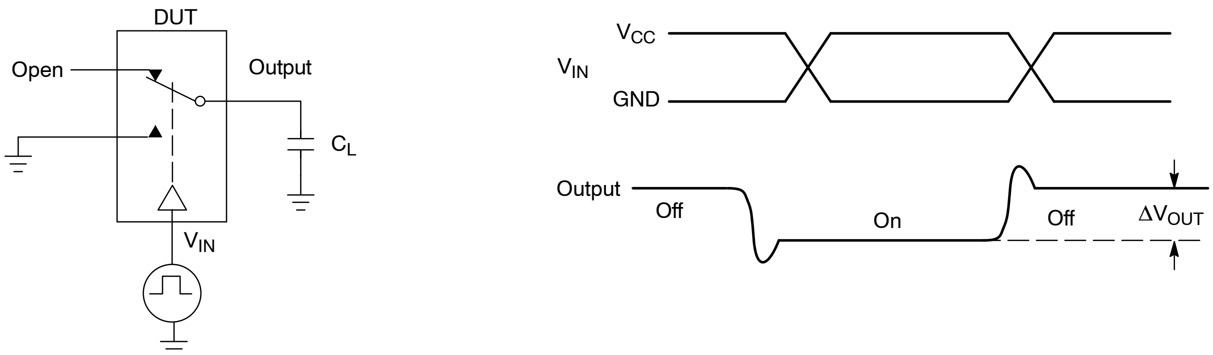


Figure 23. Charge Injection: (Q)

TYPICAL OPERATION

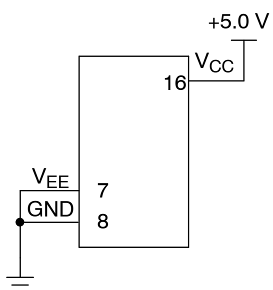


Figure 24. 5.0 Volts Single Supply
V_{CC} = 5.0 V, V_{EE} = 0

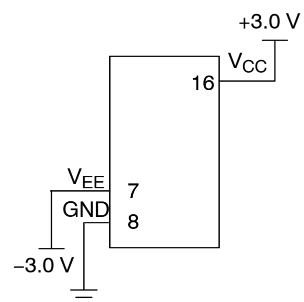
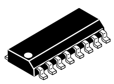


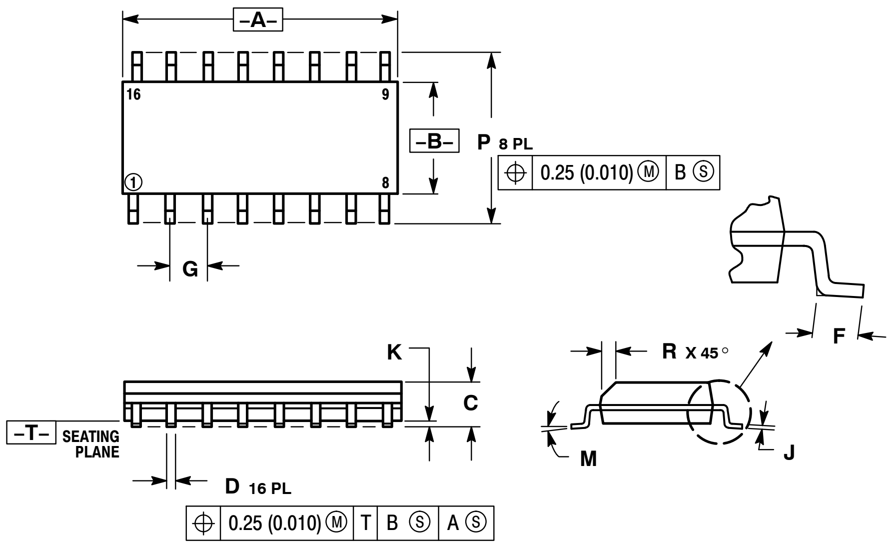
Figure 25. Dual Supply
V_{CC} = 3.0 V, V_{EE} = −3.0 V



SCALE 1:1

SOIC−16
CASE 751B−05
ISSUE K

DATE 29 DEC 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

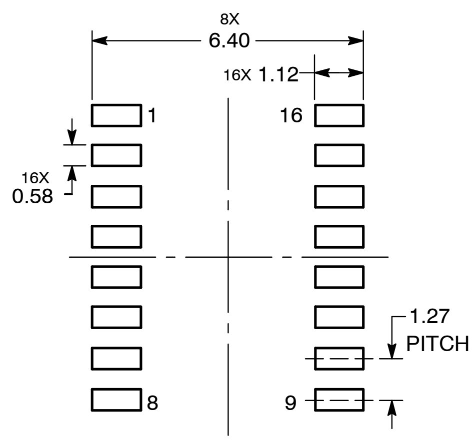
STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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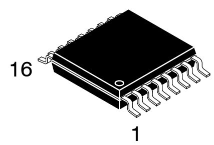
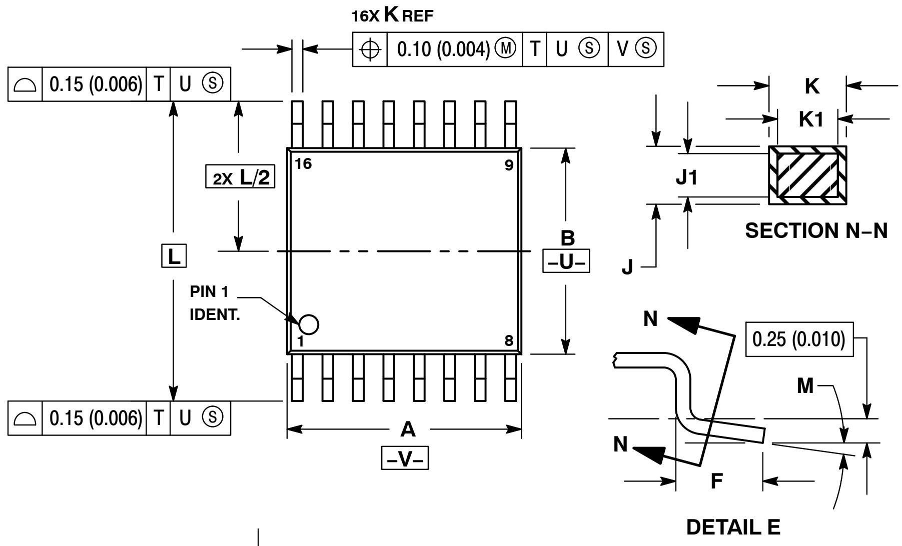
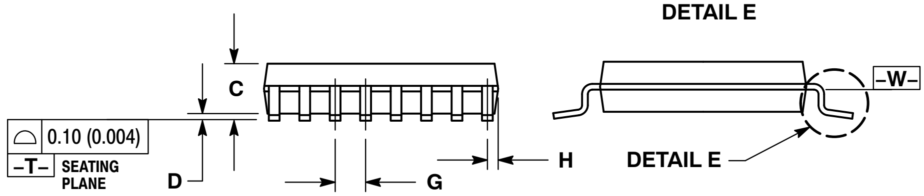


SCALE 2:1

TSSOP−16
CASE 948F−01
ISSUE B

DATE 19 OCT 2006

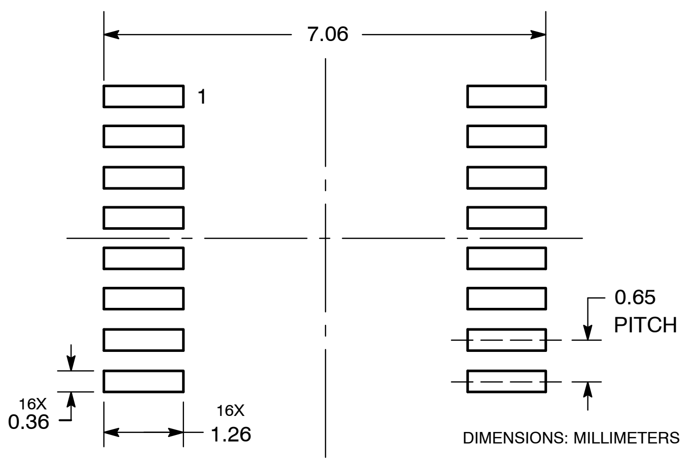




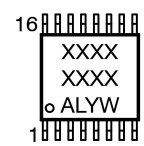
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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